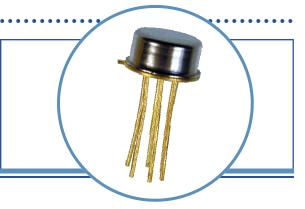


Features:

- TO-78 hermetically sealed package
- · High current transfer ratio
- 1 kV electrical isolation
- Base contact provided for conventional transistor biasing
- JAN, JANTX and JANTXV devices processed to MIL-PRF-19500
- Patent No. 4124860



Description:

Each isolator in this series consists of an infrared emitting diode and a NPN silicon phototransistor, which are mounted in a hermetically sealed TO-78 package. Devices are designed for military and/or harsh environments. The suffix letter "A" denotes the collector is electrically isolated from the case.

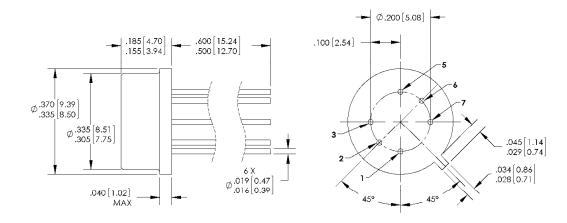
The JAN / JANTX / JANTX V 4N47, 4N47A, 4N48, 4N48A, 4N49, and 4N49A devices are processed to MIL-PRF-19500/548.

This series of 4N products are JEDEC registered, DSCC qualified.

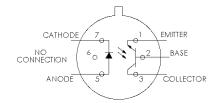
Please contact your local representative or OPTEK for more information.

Applications:

- · High-voltage isolation between input and output
- · Electrical isolation in dirty environments
- Industrial equipment
- Medical equipment
- Office



DIMENSIONS ARE IN INCHES [MIM]



Pin#	Function	Pin#	Function
3	Collector	5	Anode
2	Base	6	Open
1	Emitter	7	Cathode

BOTTOM VIEW

This product is built, tested and shipped from the USA





Absolute Maximum Rating	s (TA	= 25° C	unless	otherwise	noted)
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Storage Temperature Range	-55° C to +150° C
Operating Temperature Range	-55° C to +125° C
Input-to-Output Isolation Voltage	± 1.00 kVDC ⁽¹⁾
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽²⁾

Input Diode

Forward DC Current (65° C or below)	40 mA
Reverse Voltage	2 V
Power Dissipation	60 mW ⁽³⁾

Output Phototransistor:

Continuous Collector Current	50 mA
Collector-Emitter Voltage	40 V
Collector-Base Voltage	45 V
Emitter-Base Voltage	7.0 V
Power Dissipation	300 mW ⁽⁴⁾

Notes:

- 1. Measured with input leads shorted together and output leads shorted together.
- 2. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- 3. Derate linearly 1.0 mW/° C above 65° C.
- 4. Derate linearly 3.0 mW/° C above 25° C.

Ordering Information							
Part Number	Isolation Voltage (kV)	I _F (mA) Typ / Max	V _{CE} (Volts) Max	Processing MIL-PRF- 195000			
JAN4N47 or JAN4N47A							
JANTX4N47 or JANTX4N47A				548			
JANTXV4N47 or JANTXV4N47A							
JAN4N48 or JAN4N48A							
JANTX4N48 or JANTX4N48A	1	1 / 40	40				
JANTXV4N48 or JANTXV4N4A8							
JAN4N49 or JAN4N49A							
JANTX4N49 or JANTX4N49A							
JANTXV4N49 or JANTXV4N49A							

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Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Input Diode						
V _F	Forward Voltage	0.80 1.00 0.70	- - -	1.50 1.70 1.30	V	I _F = 10.0 mA I _F = 10.0 mA, T _A = -55° C ⁽¹⁾ I _F = 10.0 mA, T _A = -100° C ⁽¹⁾
I _R	Reverse Current	-	-	100	μA	V _R = 2.0 V
Output Phototransistor						
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	40	-	-	V	I _C = 1.0 mA, I _B = 0, I _F = 0
V _{(BR)CBO}	Collector-Base Breakdown Voltage	45	-	-	V	I _C = 100 μA, I _B = 0, I _F = 0
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	7	-	-	V	I _E = 100 μA, I _C = 0, I _F = 0
I _{C(OFF)} ¹	Collector-Emitter Dark Current	-	-	100	nA	V _{CE} = 20 V, I _B = 0, I _F = 0
I _{C(OFF)} ²	Collector-Emitter Dark Current	-	-	100	μA	V_{CE} = 20 V, I_{B} = 0, I_{F} = 0, T_{A} = 100° $C^{(1)}$
I _{CB(OFF)}	Collector-Base Dark Current	-	-	10	nA	V _{CB} = 20 V, I _E = 0, I _F = 0

Coupled

I _{C(ON)}	On-State Collector Current JAN / JANTX / JANTXV 4N47 [A]	0.50 0.70 0.50	- - -	- - -		$\begin{split} I_F &= 1.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0 \\ I_F &= 2.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0, T_A = -55^{\circ} \text{ C}^{(1)} \\ I_F &= 2.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0, T_A = 100^{\circ} \text{ C}^{(1)} \end{split}$
	JAN / JANTX / JANTXV 4N48 [A]	1.00 1.40 1.00	- - -	5 - -	mA	$\begin{aligned} &I_F = 1.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0 \\ &I_F = 2.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0, T_A = -55^{\circ} \text{ C}^{(1)} \\ &I_F = 2.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0, T_A = 100^{\circ} \text{ C}^{(1)} \end{aligned}$
	JAN / JANTX / JANTXV 4N49 [A]	2.00 2.80 2.00	- - -	10 - -		$\begin{aligned} I_F &= 1.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0 \\ I_F &= 2.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0, T_A = -55^{\circ} \text{ C}^{(1)} \\ I_F &= 2.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0, T_A = 100^{\circ} \text{ C}^{(1)} \end{aligned}$
I _{CB(ON)}	On-State Collector Base	30	-	-	μA	V _{CB} = 5 V, I _E = 0, I _F = 10 mA
V _{CE(SAT)}	Collector-Emitter Saturation Voltage JAN / JANTX / JANTXV 4N47 [A] JAN / JANTX / JANTXV 4N48 [A] JAN / JANTX / JANTXV 4N49 [A]	- - -	- - -	0.30 0.30 0.30	V	$I_F = 2.0 \text{ mA}, I_C = 0.5 \text{ mA}, I_B = 0$ $I_F = 2.0 \text{ mA}, I_C = 1.0 \text{ mA}, I_B = 0$ $I_F = 2.0 \text{ mA}, I_C = 2.0 \text{ mA}, I_B = 0$
H _{FE}	DC Current Gain	100	-	-	V	V_{CE} = 5.0 V , I_{C} = 10.0 mA, I_{F} = 0 mA
R _{IO}	Resistance (Input-to-Output)	10 ¹¹	-	-	Ω	V _{I-O} = ± 1000 VDC ⁽³⁾
C _{IO}	Capacitance (Input-to-Output)	-	-	5	pF	V _{I-O} = 0 V, f = 1.0 MHz ⁽³⁾
$T_{R,}T_{F}$	Rise and Fall Time	-	-	20	μs	V_{CC} = 10.0 V , I_F = 5.0 mA, R_L = 100 Ω

Notes

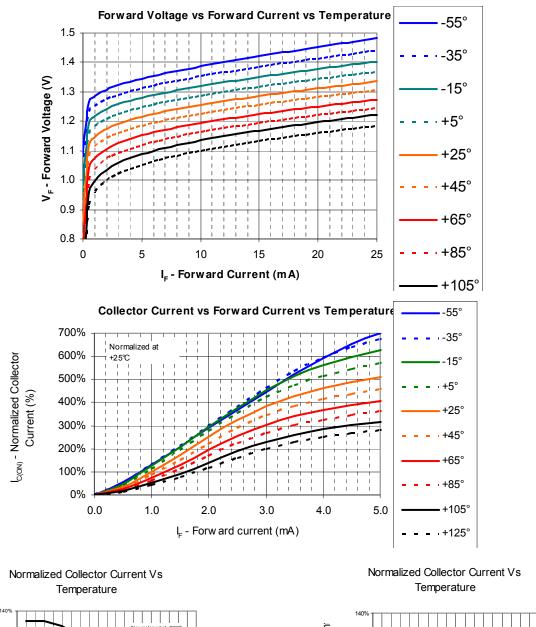
- 1. Guaranteed but not tested.
- 2. Sample tested, LTPD = 10.
- 3. Measured with input leads shorted together and output leads shorted together.

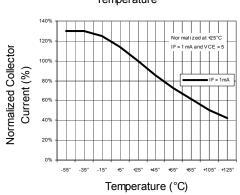
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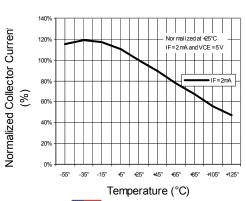




Typical Performance Curves







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